

Dual N-Ch Fast Switching MOSFETs
Description

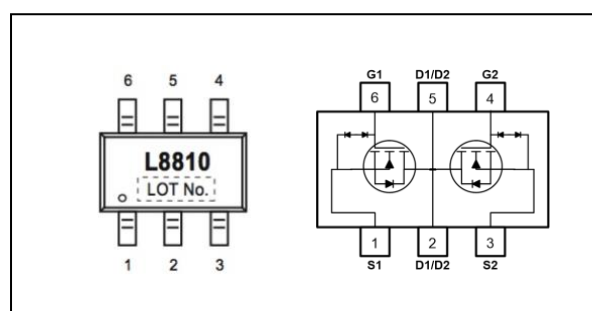
The HSW8810 is the low RDSON trenched N-CH MOSFETs with robust ESD protection. This product is suitable for Lithium-ion battery pack applications.

The HSW8810 meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- ESD Protection
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench

Product Summary

V_{DS}	20	V
$R_{DS(ON),max}$	20	mΩ
I_D	6	A

SOT23-6L Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
$I_D@T_A=25^{\circ}C$	Continuous Drain Current ¹	6	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current ¹	4.8	A
I_{DM}	Pulsed Drain Current ²	24	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ³	1.25	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	100	°C/W



N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
B _V DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =3A	15	16.5	20	mΩ
		V _{GS} =4.0V, I _D =3A	15.5	17	20.5	
		V _{GS} =3.7V, I _D =3A	16	17.5	21	
		V _{GS} =3.1V, I _D =3A	17	18.5	23	
		V _{GS} =2.5V, I _D =3A	18.5	21	26	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.5	0.7	1.2	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =16V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±8V, V _{DS} =0V	---	---	±10	uA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =3A	---	17	---	S
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _D =6A	---	10.4	---	nC
Q _{gs}	Gate-Source Charge		---	1.3	---	
Q _{gd}	Gate-Drain Charge		---	2.6	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =10V, V _{GS} =4.5V, R _G =3.3Ω I _D =3A	---	3.2	---	ns
T _r	Rise Time		---	9.8	---	
T _{d(off)}	Turn-Off Delay Time		---	31	---	
T _f	Fall Time		---	3.6	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	630	---	pF
C _{oss}	Output Capacitance		---	66	---	
C _{rss}	Reverse Transfer Capacitance		---	63	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	5.5	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	0.78	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t ≤10s.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



N-Channel Typical

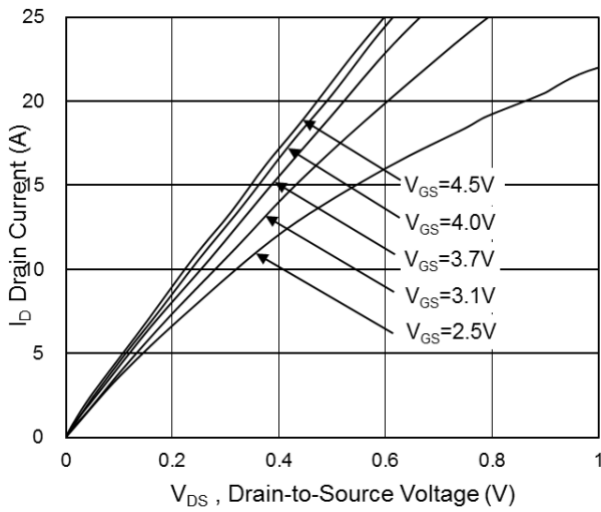


Fig.1 Typical Output Characteristics

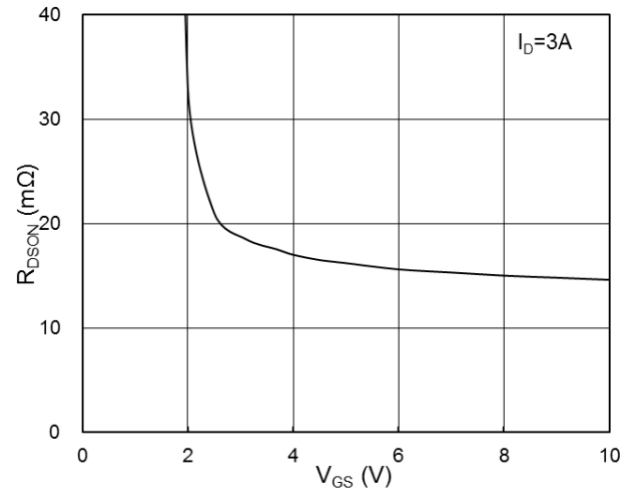


Fig.2 On-Resistance vs. Gate-Source voltage

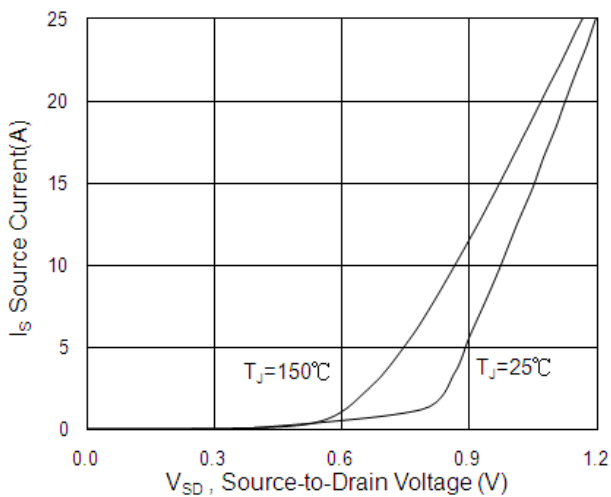


Fig.3 Forward Characteristics of Reverse

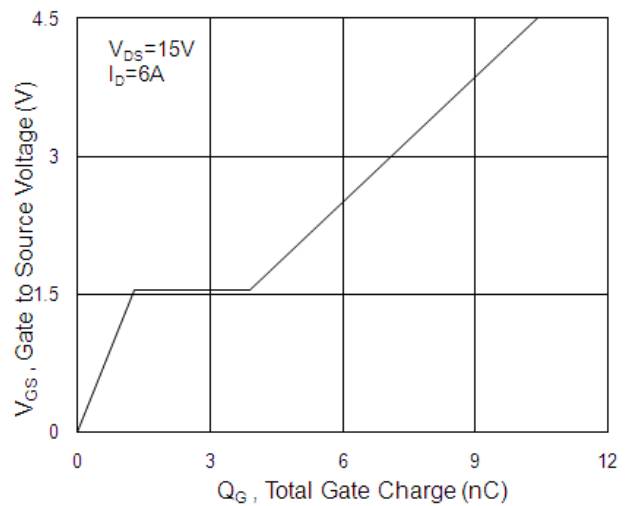


Fig.4 Gate-Charge Characteristics

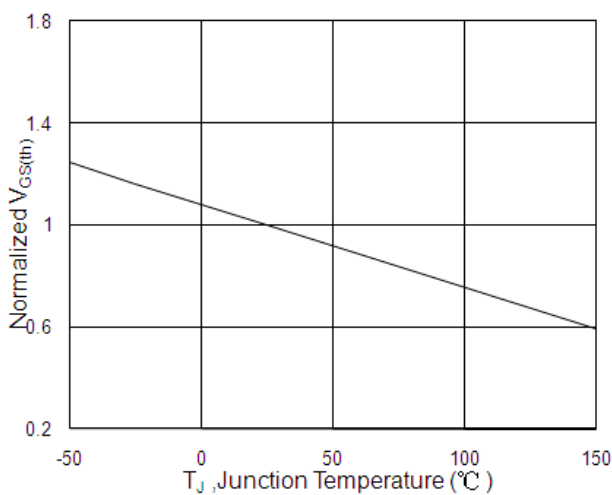


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

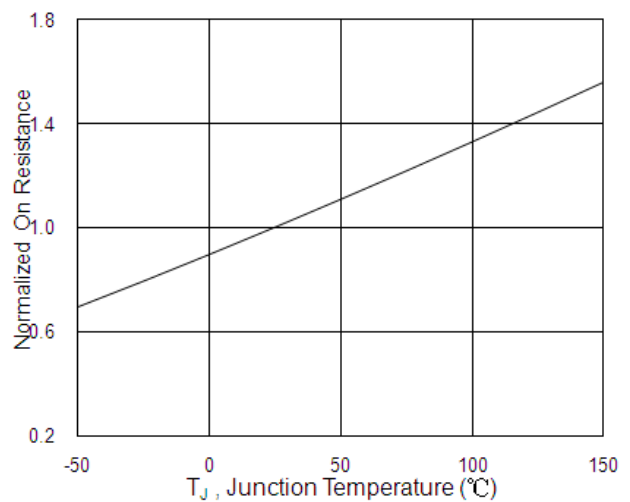


Fig.6 Normalized $R_{DS(on)}$ vs. T_J



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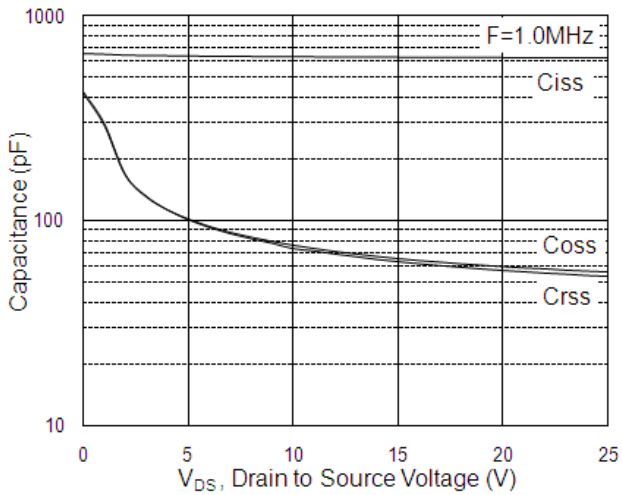


Fig.7 Capacitance

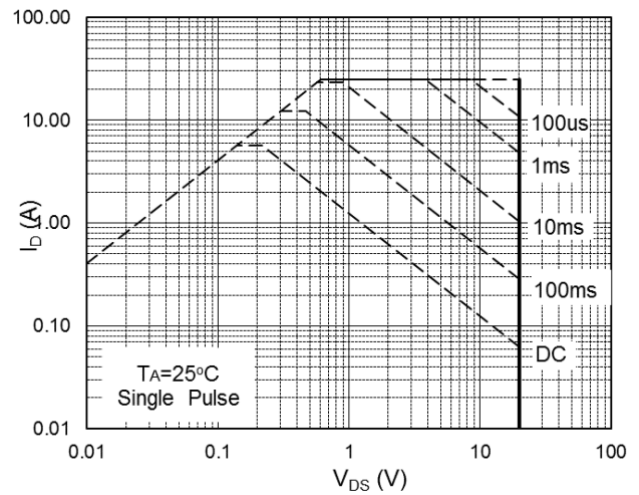


Fig.8 Safe Operating Area

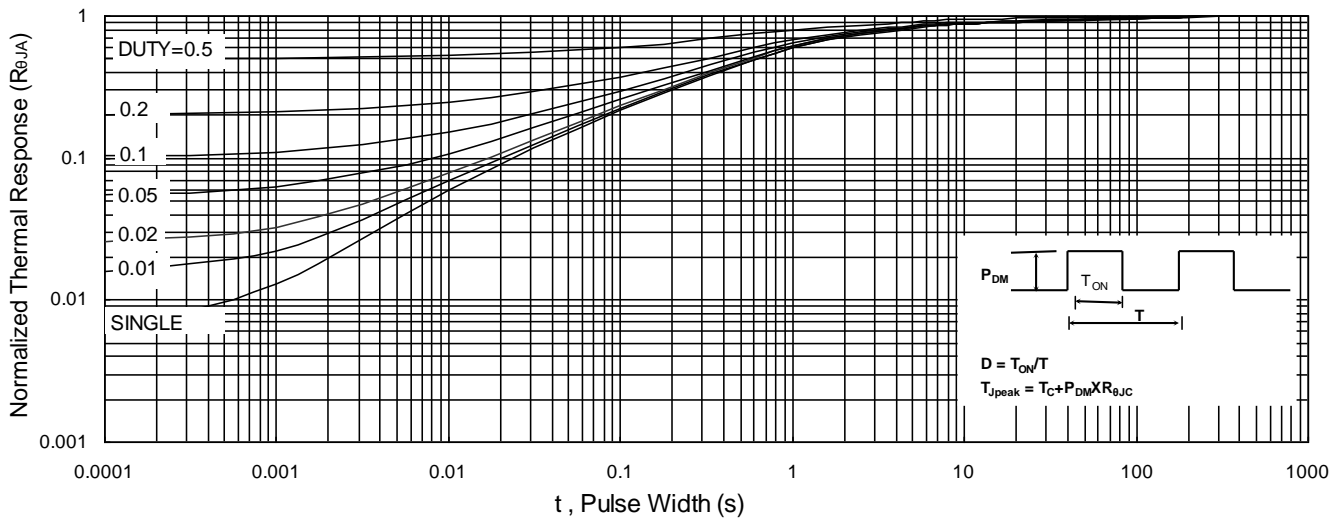


Fig.9 Normalized Maximum Transient Thermal Impedance

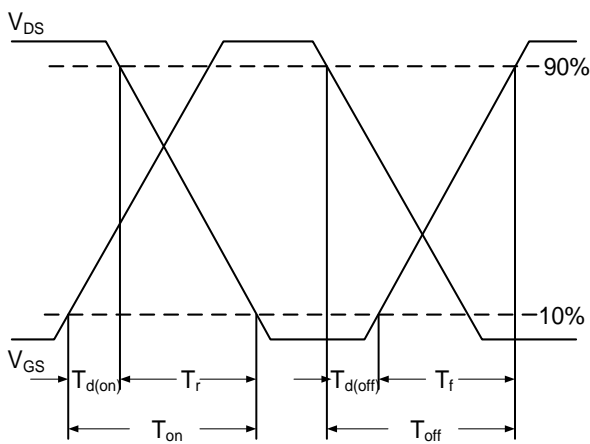


Fig.10 Switching Time Waveform

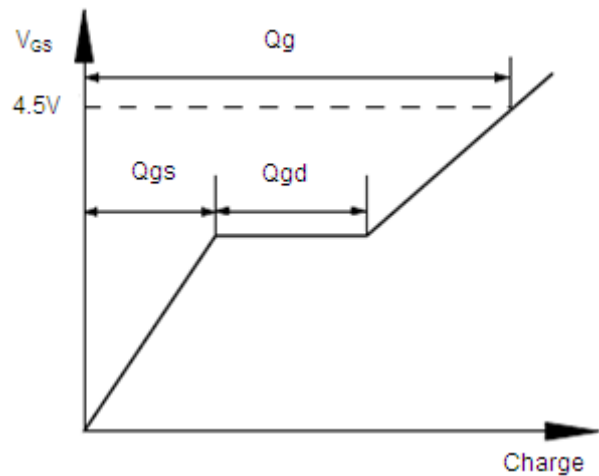
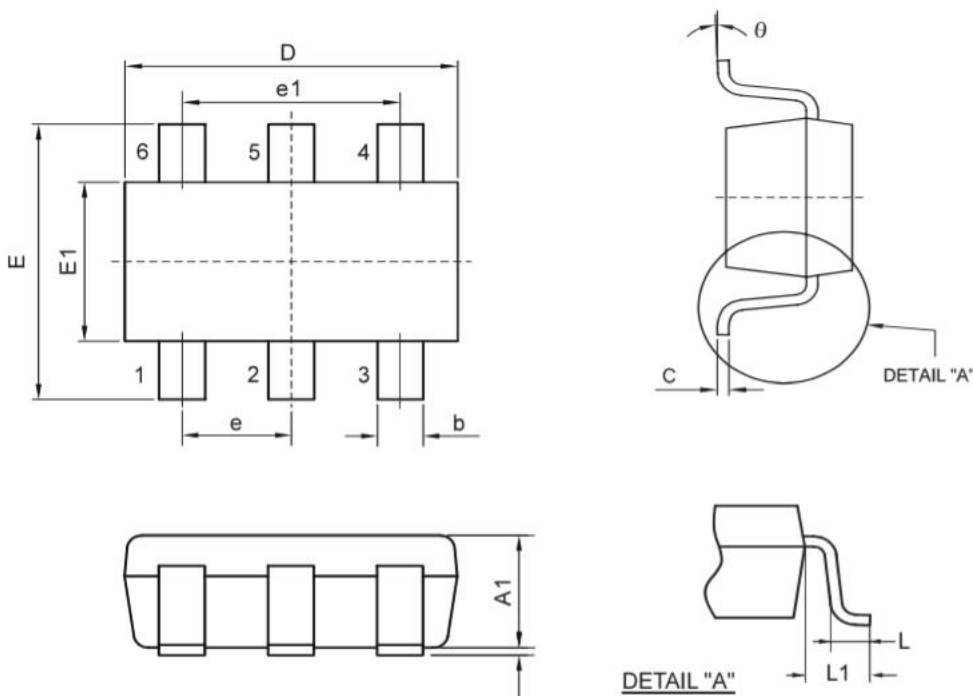


Fig.11 Gate Charge Waveform



SOT23-6L Package Outline Dimensions



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
D	2.692	3.099	0.106	0.122
E	2.591	3.000	0.102	0.118
E1	1.397	1.803	0.055	0.071
e	0.950 REF.		0.037 REF.	
e1	1.900 REF.		0.075 REF.	
b	0.300	0.500	0.012	0.020
C	0.080	0.200	0.003	0.008
A	0.000	0.100	0.000	0.004
A1	0.700	1.200	0.028	0.048
L	0.300	0.600	0.012	0.024
L1	0.600 REF.		0.023 REF.	
θ	0°	9°	0°	9°